Preferred Device

Triacs

Silicon Bidirectional Thyristors

Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS at 80°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dv/dt 500 V/µs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating di/dt 9.0 A/ms minimum at 125°C
- Pb-Free Packages are Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	$V_{ m DRM,} \ V_{ m RRM}$		V
MAC16D MAC16M MAC16N		400 600 800	
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T _C = 80°C)	I _{T(RMS)}	16	Α
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _J = 125°C)	I _{TSM}	150	Α
Circuit Fusing Consideration (t = 8.3 ms)	l ² t	93	A ² sec
Peak Gate Power (Pulse Width \leq 1.0 μ s, T _C = 80°C)	P _{GM}	20	W
Average Gate Power $(t = 8.3 \text{ ms}, T_C = 80^{\circ}\text{C})$	P _{G(AV)}	0.5	W
Operating Junction Temperature Range	T_J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



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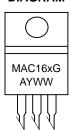
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TRIACS 16 AMPERES RMS 400 thru 800 VOLTS





MARKING DIAGRAM



TO-220AB CASE 221A-09 STYLE 4

= D, M, or N

= Assembly Location

/ = Year

WW = Work Week

G = Pb-Free Package

PIN ASSIGNMENT			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

ORDERING INFORMATION

Device	Package	Shipping
MAC16D	TO-220AB	50 Units / Rail
MAC16DG	TO-220AB (Pb-Free)	50 Units / Rail
MAC16M	TO-220AB	50 Units / Rail
MAC16MG	TO-220AB (Pb-Free)	50 Units / Rail
MAC16N	TO-220AB	50 Units / Rail
MAC16NG	TO-220AB (Pb-Free)	50 Units / Rail

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

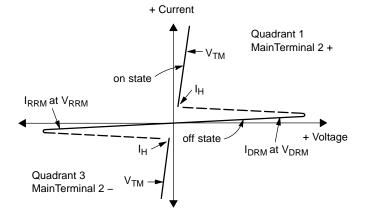
ELECTRICAL CHARACTERISTICS (T_{.1} = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Peak Repetitive Blocking Current (V _D = Rated V _{DRM} , V _{RRM} ; Gate Open)	T _J = 25°C T _J = 125°C	I _{DRM} , I _{RRM}	_ _	_ _	0.01 2.0	mA
ON CHARACTERISTICS						
Peak On-State Voltage (Note 2) (I _{TM} = ±21 A Peak)		V _{TM}	_	1.2	1.6	V
Gate Trigger Current (Continuous dc) (V_D = 12 V, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		I _{GT}	10 10 10	16 18 22	50 50 50	mA
Holding Current ($V_D = 12 \text{ V}$, Gate Open, Initiating Current = $\pm 150 \text{ mA}$)		I _H	_	20	50	mA
Latching Current (V_D = 24 V, I_G = 50 mA) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		ΙL	- - -	33 36 33	50 80 50	mA
Gate Trigger Voltage (V_D = 12 V, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		V _{GT}	0.5 0.5 0.5	0.75 0.72 0.82	1.5 1.5 1.5	V
DYNAMIC CHARACTERISTICS						
Rate of Change of Commutating Current, See Figure 10. (V_D = 400 V, I_{TM} = 6.0 A, Commutating dv/dt = 24 V/ μ s, Gate Open, T_J = 125°C, f = 250 Hz, No Snubber)	C _L = 10 μF L _L = 40 mH	(di/dt) _c	9.0	_	-	A/ms
Critical Rate of Rise of Off-State Voltage $(V_D = Rated\ V_{DRM},\ Exponential\ Waveform,\ Gate\ Open,\ T_J = 125^\circ C)$		dv/dt	500	-	-	V/μs

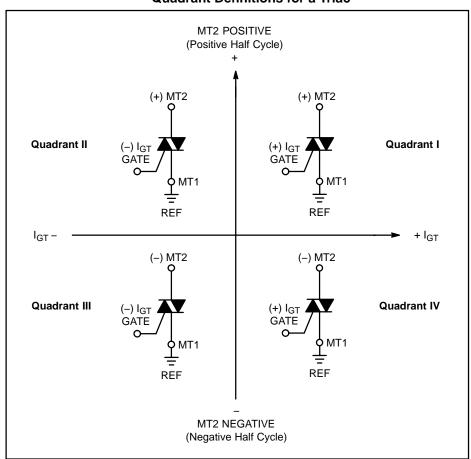
^{2.} Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

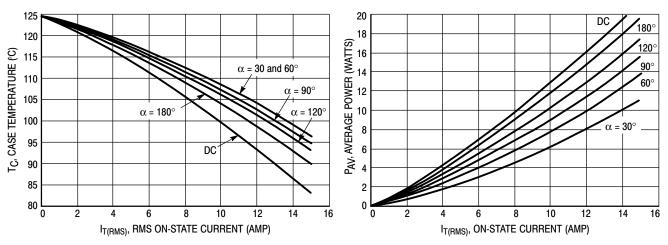
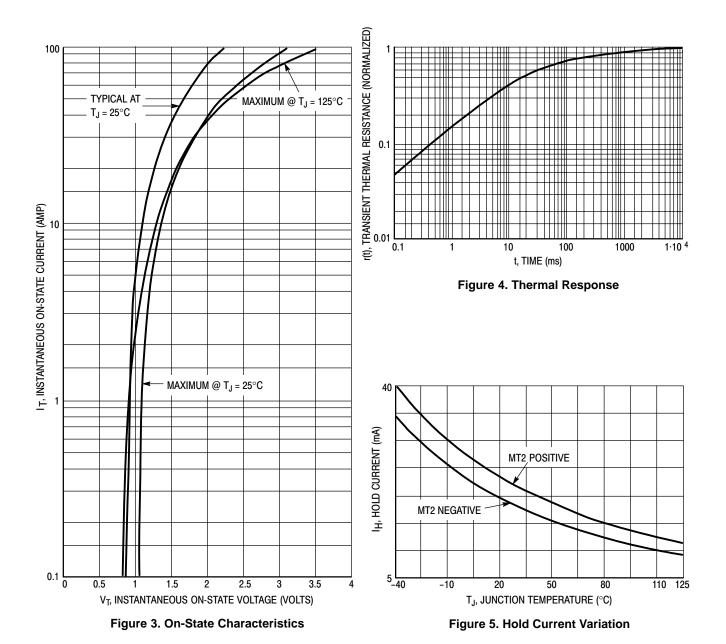
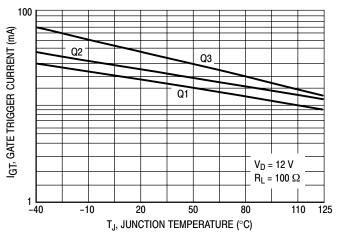


Figure 1. RMS Current Derating

Figure 2. On-State Power Dissipation



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 $V_D = 12 \text{ V}$ $R_L = 100 \Omega$ Q1

Q2

Q3

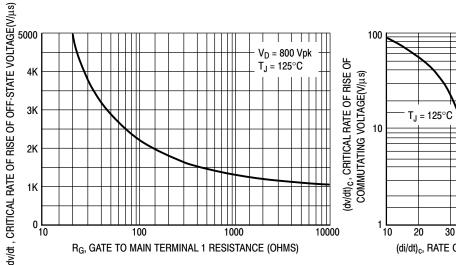
Q3

Q3

T_J, JUNCTION TEMPERATURE (°C)

Figure 6. Gate Trigger Current Variation

Figure 7. Gate Trigger Voltage Variation



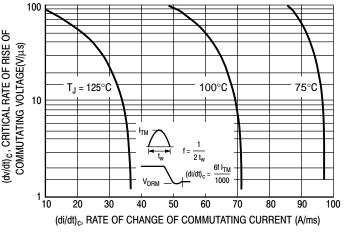
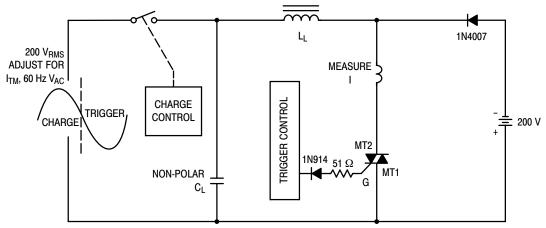


Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential Waveform)

Figure 9. Critical Rate of Rise of Commutating Voltage

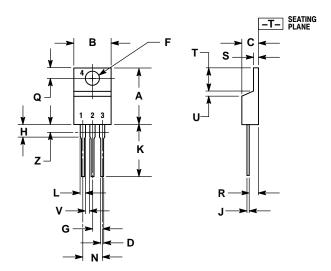


Note: Component values are for verification of rated (di/dt)_c. See AN1048 for additional information.

Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)_c

PACKAGE DIMENSIONS

TO-220AB CASE 221A-09 ISSUE AA



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 VIA 5M 1982
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 4:

PIN 1. MAIN TERMINAL 1

- 2. MAIN TERMINAL 2
- 3. GATE
- 4. MAIN TERMINAL 2

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